

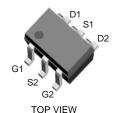
DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

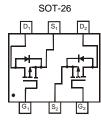
Features

- Dual P-Channel MOSFET
- Low On-Resistance
 - 150 m Ω @ $V_{GS} = -4.5V$
 - 200 m Ω @ V_{GS} = -2.5V
 - 240 mΩ @ V_{GS} = -1.8V
- Very Low Gate Threshold Voltage V_{GS(th)} ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- · Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.015 grams (approximate)





TOP VIEW Internal Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage	_	V_{GSS}	±12	V
Drain Current (Note 1)	$T_A = 25$ °C $T_A = 70$ °C	I _D	-2.0 -1.5	А
Pulsed Drain Current		I _{DM}	-7	А

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _D	600	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	208	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

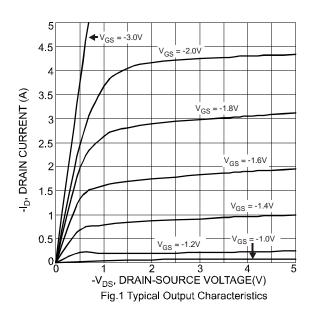


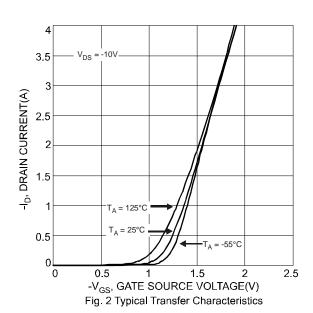
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage		BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	$T_J = 25$ °C $T_J = 125$ °C	I _{DSS}		_	-1.0 -5.0	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage		I _{GSS}		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		V _{GS(th)}	-0.45	_	-1.0	>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
				92	150		$V_{GS} = -4.5V$, $I_D = -2.0A$
Static Drain-Source On-Resistance		R _{DS (ON)}) —	134	200	mΩ	$V_{GS} = -2.5V, I_D = -1.5A$
		, ,		180	240		$V_{GS} = -1.8V, I_D = -0.5A$
Forward Transconductance		g FS		3.1	_	S	$V_{DS} = -10V, I_D = -810mA$
Diode Forward Voltage (Note 4)		V_{SD}		_	-0.9	V	$V_{GS} = 0V, I_{S} = -0.5A$
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}	_	320	_	pF	10/1/
Output Capacitance		Coss	_	80	_	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		C _{rss}	_	60	_	pF	1 = 1.0WHZ
Turn-On Delay Time			_	11.51	_	ns	
Turn-On Rise Time		t _r	_	12.09	_	ns	V _{DS} = -10V, V _{GS} = -4.5V
Turn-Off Delay Time	t _{D(off)}	_	55.34	_	ns	$R_G = 6\Omega$, $R_L = 10\Omega$	
Turn-Off Fall Time		t _f		27.54		ns	

Notes:

4. Short duration pulse test used to minimize self-heating effect.







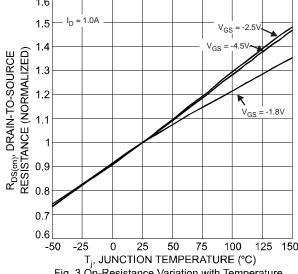
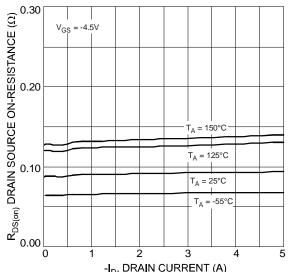


Fig. 3 On-Resistance Variation with Temperature



-I_D, DRAIN CURRENT (A) Fig. 5 Drain-Source On-Resistance Vs. Drain Current and Temperature

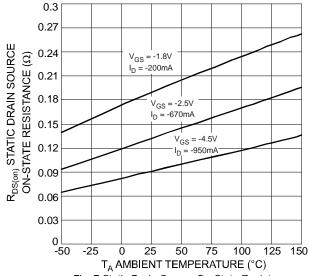


Fig. 7 Static Drain-Source On-State Resistance vs Ambient Temperature

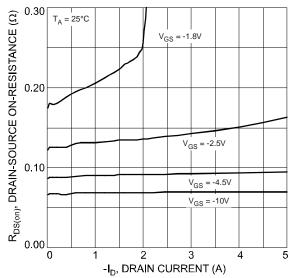
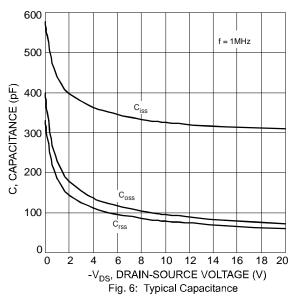


Fig. 4 On-Resistance vs Drain Current and Gate Voltage



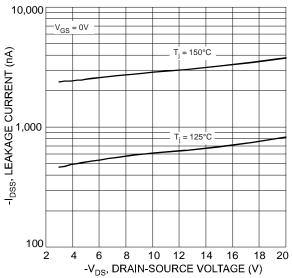
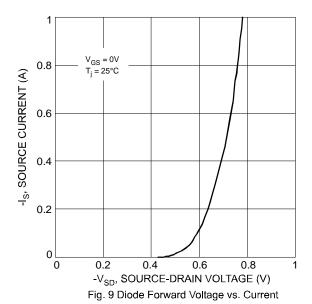


Fig. 8 Drain-Source Leakage Current vs Voltage



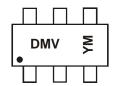


Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UDM-7	SOT-26	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

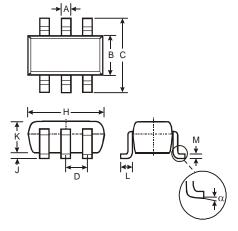


DMV = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	Ų	J	\	/	V	V		(\	1	Z	7
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

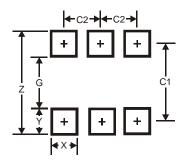
Package Outline Dimensions



	SOT-26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.10					
L	0.35	0.55	0.40				
M	0.10	0.20	0.15				
α	α 0° 8° —						
AII D	All Dimensions in mm						



Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

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